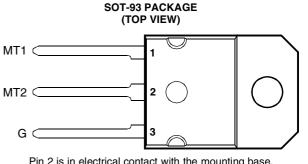
# BOURNS®

- High Current Triacs
- 25 A RMS
- Glass Passivated Wafer
- 400 V to 800 V Off-State Voltage
- 175 A Peak Current
- Max I<sub>GT</sub> of 50 mA (Quadrants 1 3)



Pin 2 is in electrical contact with the mounting base.

#### absolute maximum ratings over operating case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT
TIC263D		400	
Depetitive peak off state voltage (see Nate 1)		600	V
Repetitive peak off-state voltage (see Note 1) TIC 263S	VDRM	700	
TIC263N		800	
Full-cycle RMS on-state current at (or below) 60°C case temperature (see Note 2)	I <sub>T(RMS)</sub>	25	A
Peak on-state surge current full-sine-wave at (or below) 25°C case temperature (see Note 3)	I <sub>TSM</sub>	175	A
Peak gate current	I <sub>GM</sub>	±1	A
Operating case temperature range	т <sub>с</sub>	-40 to +110	°C
Storage temperature range	T <sub>stg</sub>	-40 to +125	°C
Lead temperature 1.6 mm from case for 10 seconds	TL	230	°C

NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.

2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 60°C derate linearly to 110°C case temperature at the rate of 500mA/°C.

3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of peak reverse volta ge and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.

## electrical characteristics at 25°C case temperature (unless otherwise noted )

	PARAMETER	TEST CONDITIONS			MIN	ТҮР	MAX	UNIT
I <sub>DRM</sub>	Repetitive peak off-state current	V <sub>D</sub> = Rated V <sub>DRM</sub>	$I_{G} = 0$	T <sub>C</sub> = 110°C			±2	mA
I <sub>GT</sub>		V <sub>supply</sub> = +12 V†	$R_L = 10 \Omega$	t <sub>p(g)</sub> > 20 μs		15	50	mA
	Gate trigger	V <sub>supply</sub> = +12 V†	$R_L = 10 \Omega$	t <sub>p(g)</sub> > 20 μs		-30	-50	
	current	$V_{supply} = -12 V^{\dagger}$	$R_L = 10 \Omega$	t <sub>p(g)</sub> > 20 μs		-20	-50	
		V <sub>supply</sub> = -12 V†	$R_L = 10 \Omega$	t <sub>p(g)</sub> > 20 μs		32		
V <sub>GT</sub>		V <sub>supply</sub> = +12 V†	$R_L = 10 \Omega$	t <sub>p(g)</sub> > 20 μs		0.8	2	v
	Gate trigger	$V_{supply} = +12 V^{\dagger}$	$R_L = 10 \Omega$	t <sub>p(g)</sub> > 20 μs		-0.8	-2	
	voltage	V <sub>supply</sub> = -12 V†	$R_L = 10 \Omega$	t <sub>p(g)</sub> > 20 μs		-0.8	-2	
		V <sub>supply</sub> = -12 V†	$R_L = 10 \Omega$	t <sub>p(g)</sub> > 20 μs		0.8	2	
V <sub>T</sub>	On-state voltage	I <sub>T</sub> = ±35.2 A	l <sub>G</sub> = 50 mA	(see Note 4)		±1.5	±1.7	V

† All voltages are with respect to Main Terminal 1.

NOTE 4: This parameter must be measured using pulse techniques,  $t_p = \le 1$  ms, duty cycle  $\le 2$  %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

## PRODUCT INFORMATION

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## electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

	PARAMETER		TEST CONDITIONS			ТҮР	MAX	UNIT
l	Holding current	V <sub>supply</sub> = +12 V†	l <sub>G</sub> = 0	Init' I <sub>T</sub> = 100 mA		20	40	mA
Ч		V <sub>supply</sub> = -12 V†	$I_{G} = 0$	Init' I <sub>T</sub> = -100 mA		-10	-40	
IL.	Latching current	V <sub>supply</sub> = +12 V†	(see Note 5)			20		mA
		V <sub>supply</sub> = -12 V†			-20			
dv/dt	Critical rate of rise of	V <sub>D</sub> = Rated V <sub>D</sub>	I <sub>G</sub> = 0	T <sub>C</sub> = 110°C		±450		V/µs
uv/ut	off-state voltage			1 <sub>C</sub> = 110 0				
dy/dt	Critical rise of	V <sub>D</sub> = Rated V <sub>D</sub>		$T_{\rm C} = 80^{\circ}{\rm C}$		±1		V/µs
dv/dt <sub>(c)</sub>	commutation voltage	$di/dt = 0.5 I_{T(RMS)}/ms$		$I_T = 1.4 I_{T(RMS)}$				v/µs
di/dt	Critical rate of rise of	V <sub>D</sub> = Rated V <sub>D</sub>	I <sub>GT</sub> = 50 mA	$I_{GT} = 50 \text{ mA}$ $T_{C} = 110^{\circ}\text{C}$		±100		A/µs
	on -state current	di <sub>G</sub> /dt = 50 mA/µs		1 <sub>C</sub> = 110 0				-π/μ5

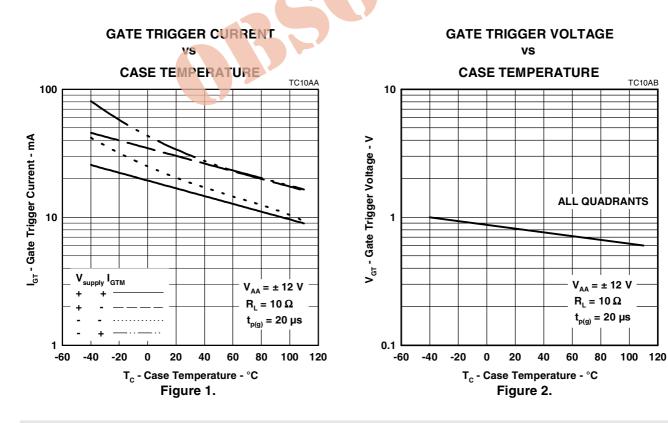
† All voltages are with respect to Main Terminal 1.

NOTE 5: The triacs are triggered by a 15-V (open-circuit amplitude) pulse supplied by a generator with the following characteristics:  $R_G = 100 \ \Omega$ ,  $t_{p(g)} = 20 \ \mu s$ ,  $t_r = \le 15 \ ns$ ,  $f = 1 \ kHz$ .

#### thermal characteristics

PARAMETER			TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			1.52	°C/W
$R_{\thetaJA}$	Junction to free air thermal resistance			36	°C/W

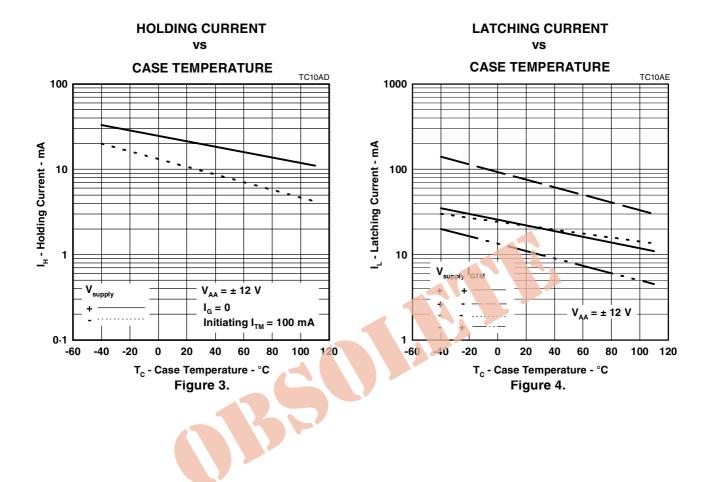




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#### **TYPICAL CHARACTERISTICS**



## PRODUCT INFORMATION